



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: [info@chipsmall.com](mailto:info@chipsmall.com) Web: [www.chipsmall.com](http://www.chipsmall.com)

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



# TrenchMV™ IXTL2x220N075T

## Power MOSFETs

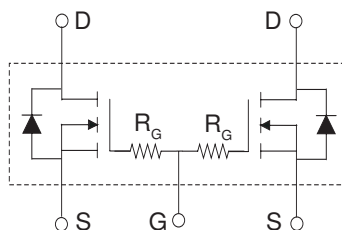
### Common-Gate Pair

(Electrically Isolated Back Surface)

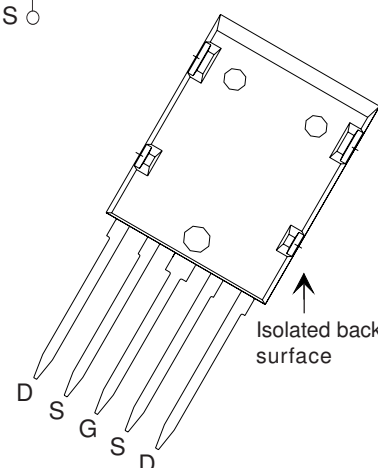
N-Channel Enhancement Mode

Avalanche Rated

$$\begin{aligned} V_{DSS} &= 75 \text{ V} \\ I_{D25} &= 2 \times 120 \text{ A} \\ R_{DS(on)} &\leq 5.5 \text{ m}\Omega \end{aligned}$$



ISOPLUSi5-Pak™ (IXTL)



G = Gate  
S = Source  
D = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	75	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	75	V
$V_{GSM}$	Transient	$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ (Combined die total = 240 A)	120	A
$I_{LRMS}$	Package Current Limit, RMS (Combined die total = 150 A)	75	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	600	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	25	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.0	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$ , $R_G = 3.3 \Omega$	3	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	150	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 seconds	260	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, $t = 1$ minute, $I_{ISOL} < 1 \text{ mA}$ , RMS	2500	V
$F_C$	Mounting force	20..120/4.5..25	N/lb.
Weight		9	g

Test Conditions		Characteristic Values		
$(T_J = 25^\circ\text{C}$ unless otherwise specified)		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 50 \text{ A}$ , Notes 1, 2			5.5 m $\Omega$

#### Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- 175  $^\circ\text{C}$  Operating Temperature

#### Advantages

- Easy to mount
- Space savings
- High power density

#### Applications

- Automotive
  - Motor Drives
  - 42V Power Bus
  - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- High Current Switching Applications

All ratings and parametric values are per each MOSFET die unless otherwise specified.

DS99750(01/07)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = 60\text{ A}$ , Note 1	75	120	S
$R_G$			3	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		7700	pF
$C_{oss}$			1100	pF
$C_{rss}$			230	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 25\text{ A}$ $R_G = 3.3\ \Omega$ (External)		29	ns
$t_r$			65	ns
$t_{d(off)}$			55	ns
$t_f$			47	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 25\text{ A}$		165	nC
$Q_{gs}$			40	nC
$Q_{gd}$			50	nC
$R_{thJC}$				1.0 $^\circ\text{C/W}$
$R_{thCS}$		0.5		$^\circ\text{C/W}$

## Source-Drain Diode

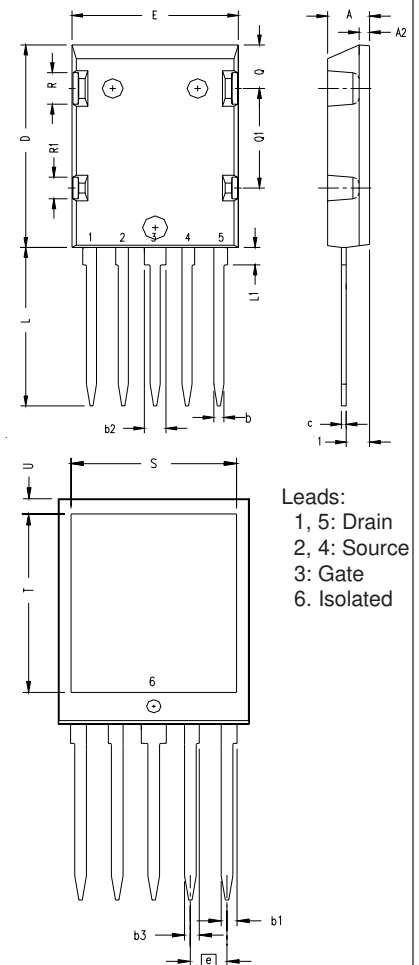
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			220 A
$I_{SM}$	Pulse width limited by $T_{JM}$			600 A
$V_{SD}$	$I_F = 50\text{ A}$ , $V_{GS} = 0\text{ V}$ , Note 1			1.0 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 40\text{ V}$ , $V_{GS} = 0\text{ V}$		50	ns

- Notes: 1. Pulse test:  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$ ;  
 2. Drain and Source Kelvin contacts must be located less than 5 mm from the plastic body.

## ADVANCETECHNICALINFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

## ISOPLUS i5-Pak™ (IXTL) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.063	.072	1.60	1.83
b2	.100	.110	2.54	2.79
b3	.058	.068	1.47	1.73
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

## Note:

1. TAB 6 - Electrically isolated from the other pins.  
 2. All leads and tab are tin plated.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2  
 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537